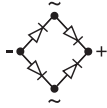
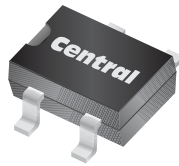


CBR1-D020S SERIES**SURFACE MOUNT
1 AMP
SILICON BRIDGE RECTIFIER**www.centrasemi.com**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CBR1-D020S series types are silicon full wave bridge rectifiers mounted in a durable epoxy surface mount molded case, utilizing glass passivated chips.

NOTE: Also available in Fast Recovery, please contact factory for details.

MARKING: FULL PART NUMBER**SMDIP CASE****MAXIMUM RATINGS:**

($T_A=25^{\circ}\text{C}$ unless otherwise noted)

	SYMBOL	CBR1-D020S	CBR1-D040S	CBR1-D060S	CBR1-D080S	CBR1-D100S	UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	200	400	600	800	1000	V
DC Blocking Voltage	V_R	200	400	600	800	1000	V
RMS Reve	$V_{R(RMS)}$	140	280	420	560	700	V
Average Forward Current ($T_A=50^{\circ}\text{C}$)	I_O			1.0			A
Peak Forward Surge Current	I_{FSM}			50			A
Rating for Fusing ($t<8.35\text{ms}$)	I^2t			10			A^2s
Operating and Storage Junction Temperature	T_J, T_{stg}			-65 to +150			$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_R	$V_R=\text{Rated } V_{RRM}$			10	μA
I_R	$V_R=\text{Rated } V_{RRM}, T_A=125^{\circ}\text{C}$			0.5	mA
V_F	$I_F=1.0\text{A}$			1.1	V
C_J	$V_R=4.0\text{V}, f=1.0\text{MHz}$		25		pF

CBR1-D020S SERIES

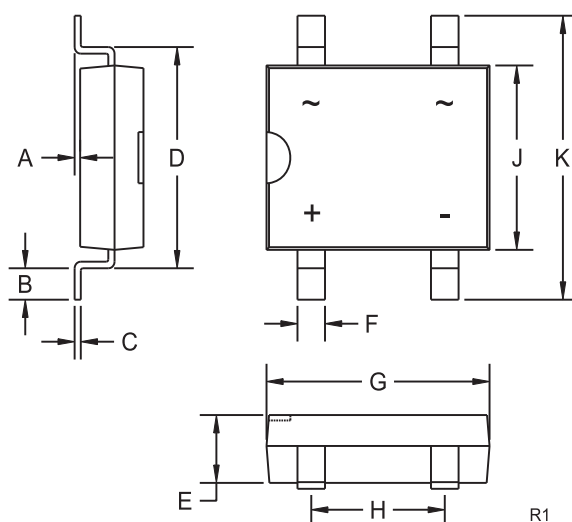
SURFACE MOUNT

1 AMP

SILICON BRIDGE RECTIFIER



SMDIP CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.008	0.10	0.20
B	0.040	0.060	1.02	1.52
C	0.009		0.23	
D	0.290	0.310	7.37	7.87
E	0.086	0.098	2.18	2.49
F	0.038	0.042	0.97	1.07
G	0.316	0.335	8.03	8.51
H	0.195	0.205	4.95	5.21
J	0.245	0.255	6.22	6.48
K	0.360	0.410	9.14	10.41

SMDIP (REV: R1)

MARKING: FULL PART NUMBER

R3 (4-January 2010)